

N- and P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY

	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
N-Channel	12	0.017 at V _{GS} = 4.5 V	11.8
		0.025 at V _{GS} = 2.5 V	9.8
P-Channel	- 12	0.032 at V _{GS} = - 4.5 V	- 8.9
		0.053 at V _{GS} = - 2.5 V	- 6.9

FEATURES

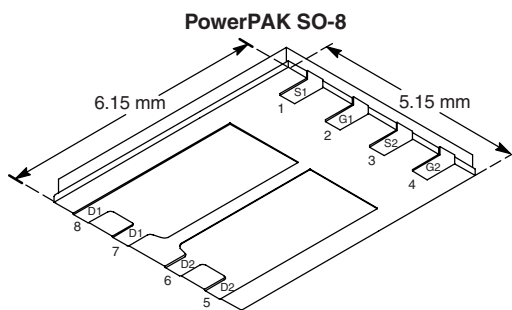
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFETs
- New Low Thermal Resistance PowerPAK® Package with Low 1.07 mm Profile
- PWM Optimized for High Efficiency
- 100 % R_g Tested



RoHS
COMPLIANT
HALOGEN
FREE
Available

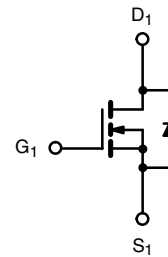
APPLICATIONS

- Point-of-Load Synchronous Rectifier
- 5 V or 3.3 V BUS Step Down
- Q_g Optimized for 500 kHz Operation
- Synchronous Buck, Shoot-Thru Resistant

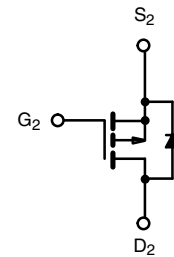


Bottom View

Ordering Information: Si7540DP-T1-E3 (Lead (Pb)-free)
Si7540DP-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

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Parameter		Symbol	N-Channel		P-Channel		Unit
			10 s	Steady	10 s	Steady	
Drain-Source Voltage		V _{DS}	12		- 12		V
Gate-Source Voltage		V _{GS}	± 8				
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	11.8	7.6	- 8.9	- 5.7	A
	T _A = 70 °C		9.5	6.1	- 7.1	- 4.6	
Pulsed Drain Current		I _{DM}	20				
Continuous Source Current (Diode Conduction) ^a		I _S	2.9	1.1	- 2.9	- 1.1	
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	3.5	1.4	3.5	1.4	W
	T _A = 70 °C		2.2	0.9	2.2	0.9	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150				°C
Soldering Recommendations (Peak Temperature) ^{b,c}			260				

THERMAL RESISTANCE RATINGS

Parameter	Symbol	N-Channel		P-Channel		Unit
		Typical	Maximum	Typical	Maximum	
Maximum Junction-to-Ambient ^a	R _{thJA}	26	35	26	35	°C/W
		60	85	60	85	
Maximum Junction-to-Case (Drain)	R _{thJC}	3.9	5.5	3.9	5.5	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Condition		Min.	Typ.	Max.	Unit
Static							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	N-Ch	0.6		1.5	V
		V _{DS} = V _{GS} , I _D = - 250 μA	P-Ch	- 0.6		- 1.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V	N-Ch P-Ch			± 100 ± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 12 V, V _{GS} = 0 V	N-Ch			1	μA
		V _{DS} = - 12 V, V _{GS} = 0 V	P-Ch			- 1	
		V _{DS} = 12 V, V _{GS} = 0 V, T _J = 55 °C	N-Ch			5	
		V _{DS} = - 12 V, V _{GS} = 0 V, T _J = 55 °C	P-Ch			- 5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 4.5 V	N-Ch	20			A
		V _{DS} ≤ - 5 V, V _{GS} = - 4.5 V	P-Ch	- 20			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 11.8 A	N-Ch		0.014	0.017	Ω
		V _{GS} = - 4.5 V, I _D = - 8.9 A	P-Ch		0.026	0.032	
		V _{GS} = 2.5 V, I _D = 9.8 A	N-Ch		0.020	0.025	
		V _{GS} = - 2.5 V, I _D = - 6.9 A	P-Ch		0.043	0.053	
Forward Transconductance ^a	g _{fs}	V _{DS} = 5 V, I _D = 11.8 A	N-Ch		32		S
		V _{DS} = - 5 V, I _D = - 8.9 A	P-Ch		23		
Diode Forward Voltage ^a	V _{SD}	I _S = 2.9 A, V _{GS} = 0 V	N-Ch		0.77	1.2	V
		I _S = - 2.9 A, V _{GS} = 0 V	P-Ch		- 0.8	- 1.2	
Dynamic ^b							
Total Gate Charge	Q _g	N-Channel V _{DS} = 6 V, V _{GS} = 4.5 V, I _D = 11.8 A	N-Ch P-Ch		11.5 13	17 20	nC
Gate-Source Charge	Q _{gs}		N-Ch P-Ch		3.2 4.1		
Gate-Drain Charge	Q _{gd}	P-Channel V _{DS} = - 6 V, V _{GS} = - 4.5 V, I _D = - 8.9 A	N-Ch P-Ch		2.5 1.9		
Gate Resistance	R _g		N-Ch P-Ch	0.5 1.5	1.7 3.5	2.5 5.6	Ω
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 6 V, R _L = 6 Ω I _D ≅ 1 A, V _{GEN} = 4.5 V, R _g = 6 Ω	N-Ch P-Ch		30 35	45 55	ns
Rise Time	t _r		N-Ch P-Ch		50 42	75 65	
Turn-Off Delay Time	t _{d(off)}	P-Channel V _{DD} = - 6 V, R _L = 6 Ω I _D ≅ - 1 A, V _{GEN} = - 4.5 V, R _g = 6 Ω	N-Ch P-Ch		60 54	90 85	
Fall Time	t _f		N-Ch P-Ch		25 17	40 30	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.9 A, dI/dt = 100 A/μs	N-Ch		40	80	
		I _F = - 2.9 A, dI/dt = 100 A/μs	P-Ch		40	80	

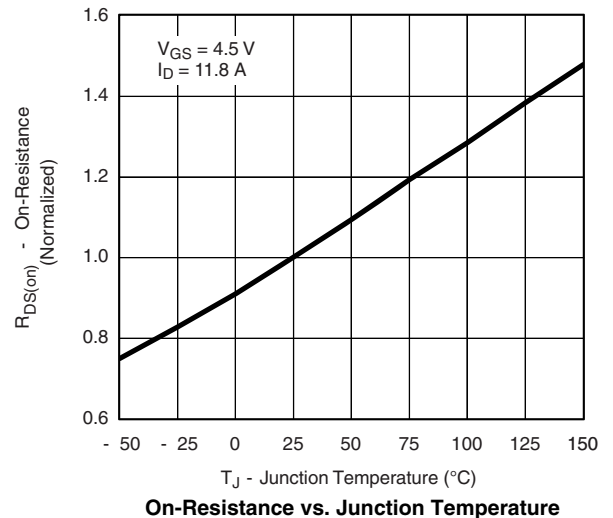
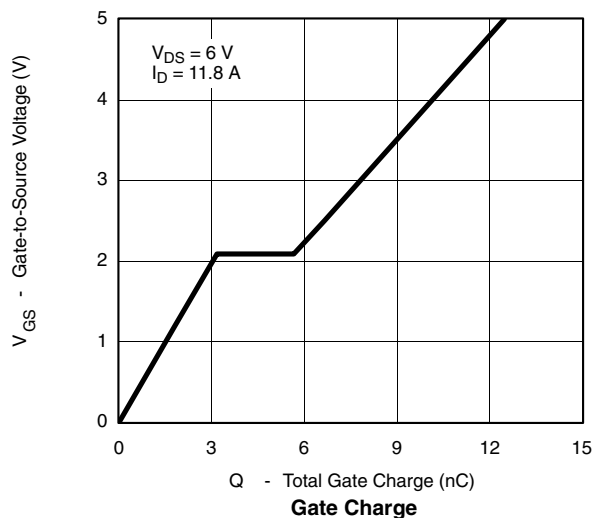
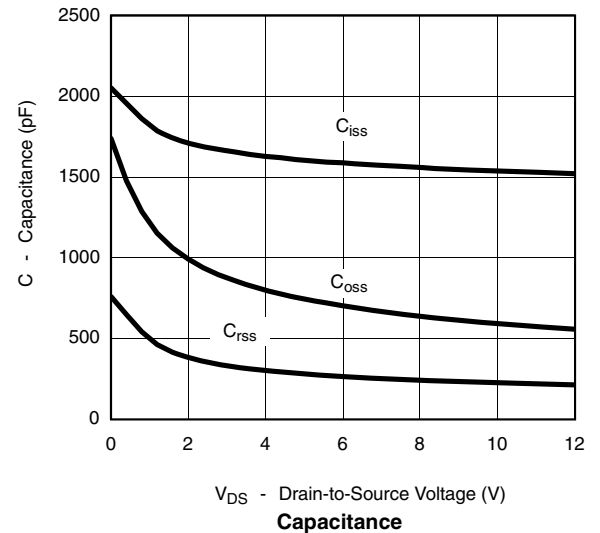
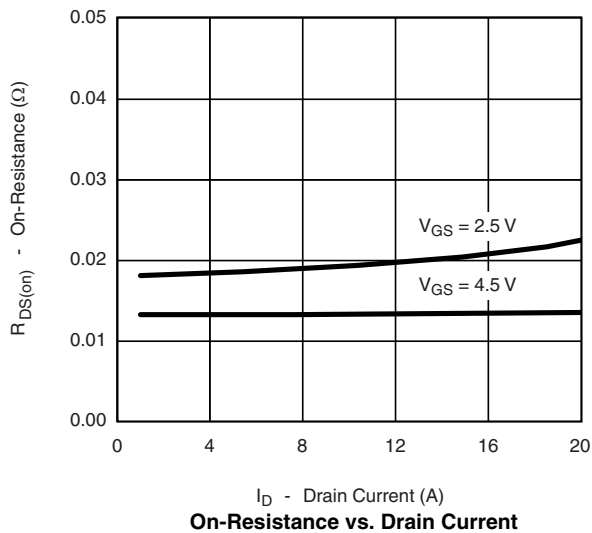
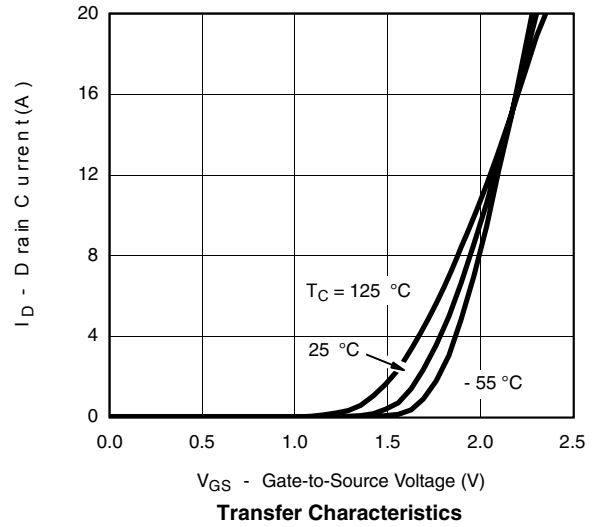
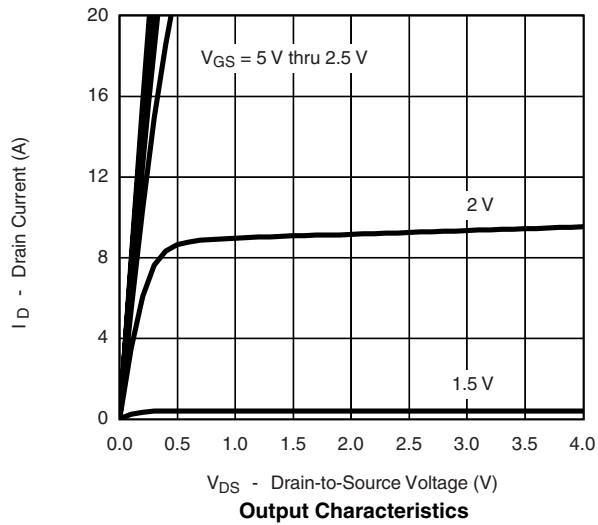
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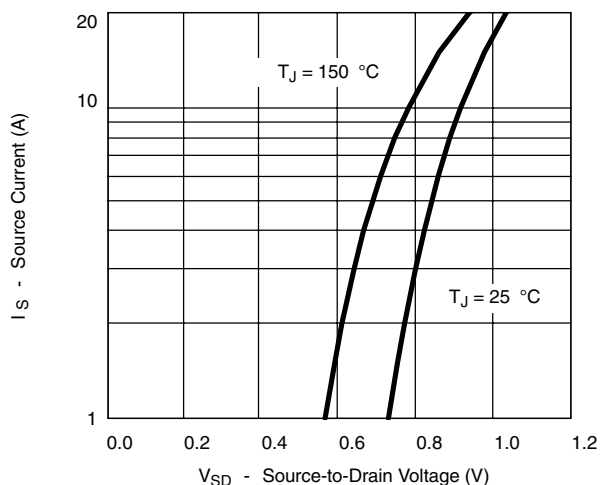
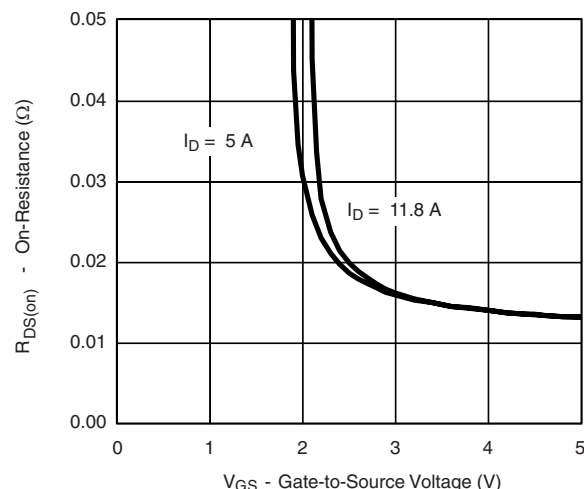
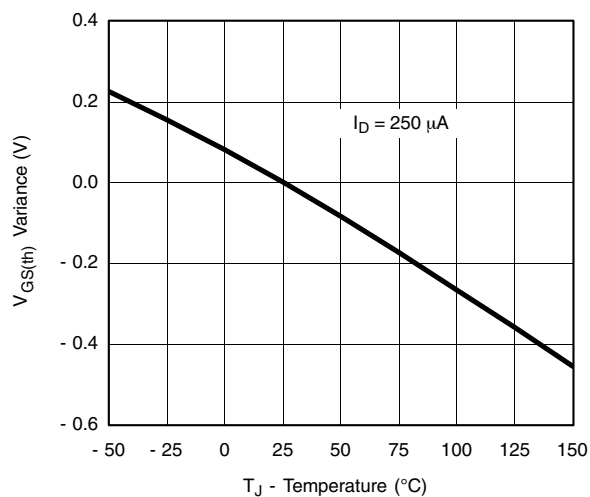
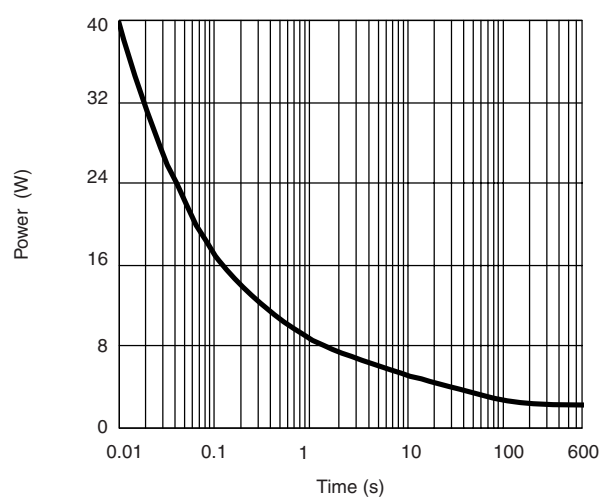
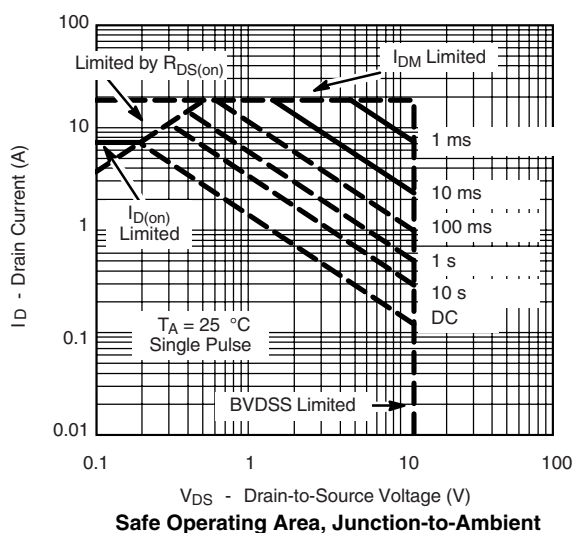
a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

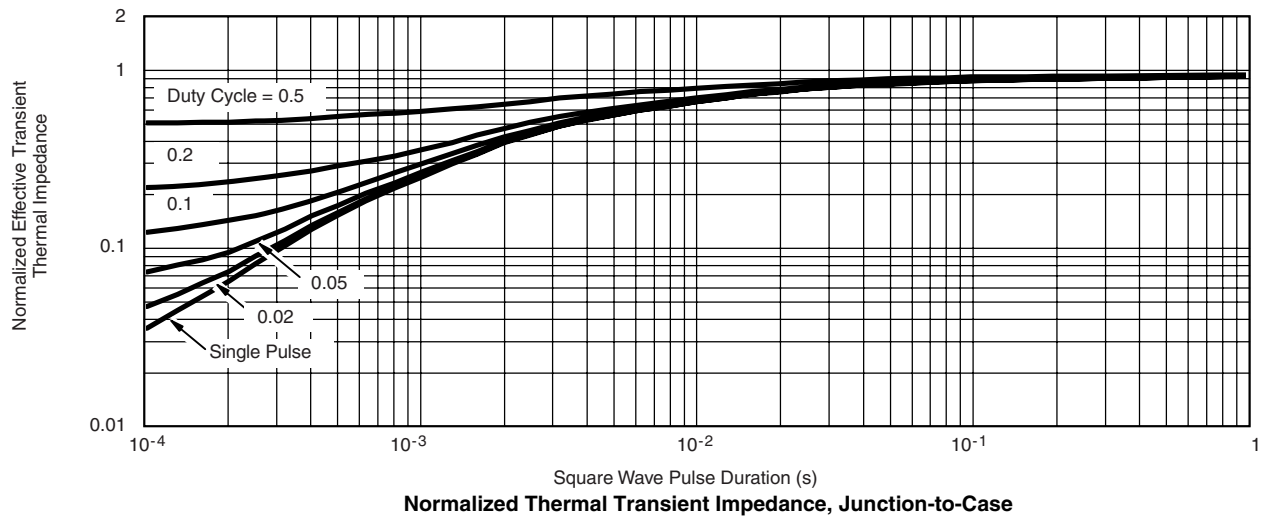
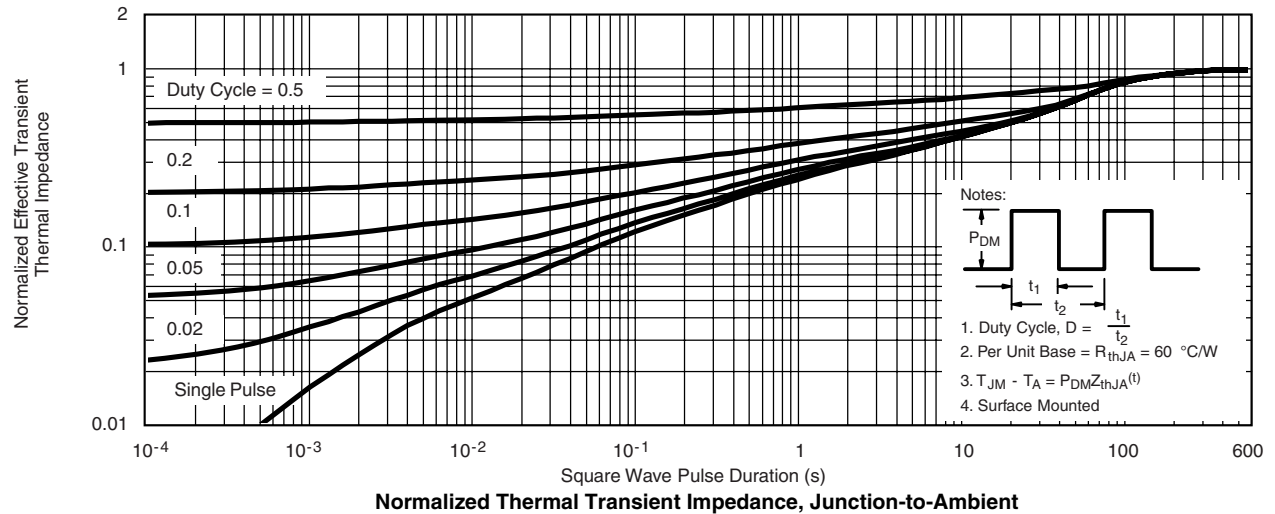
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

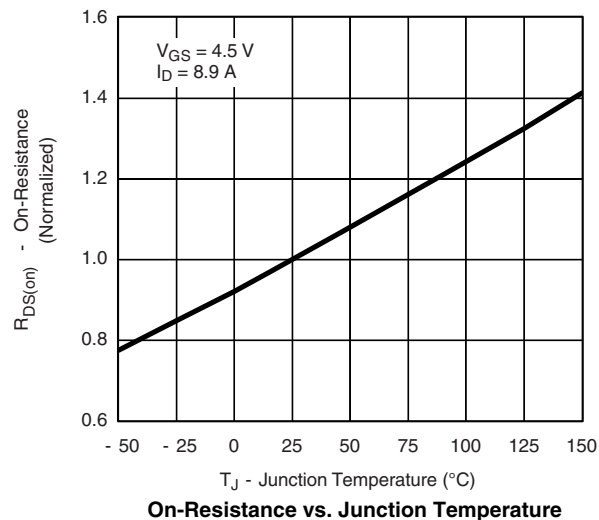
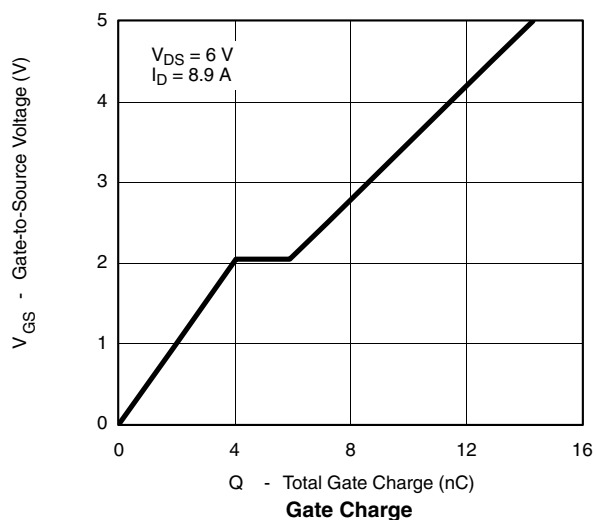
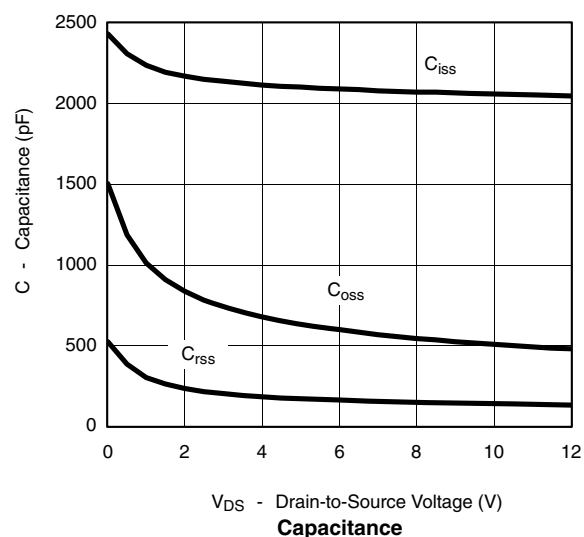
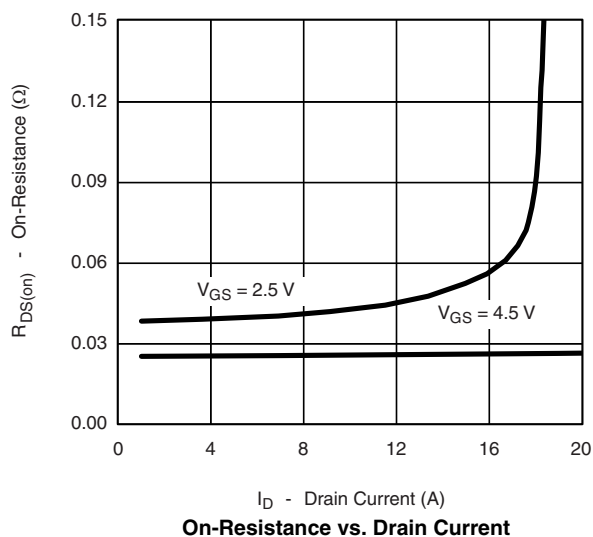
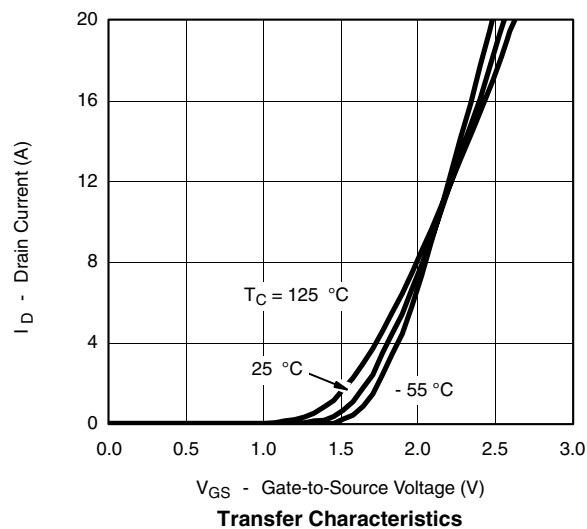
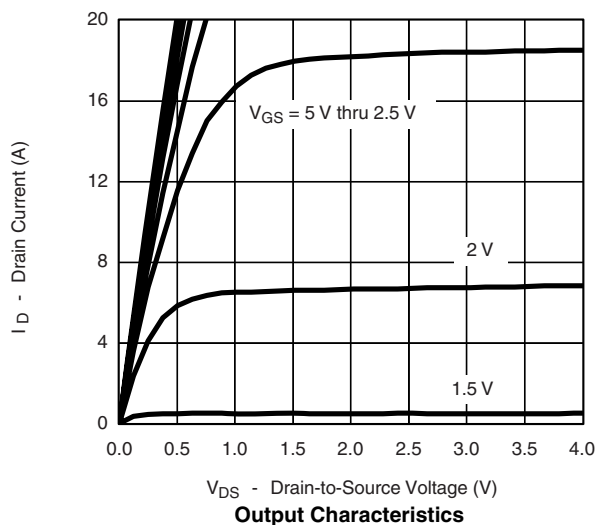
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



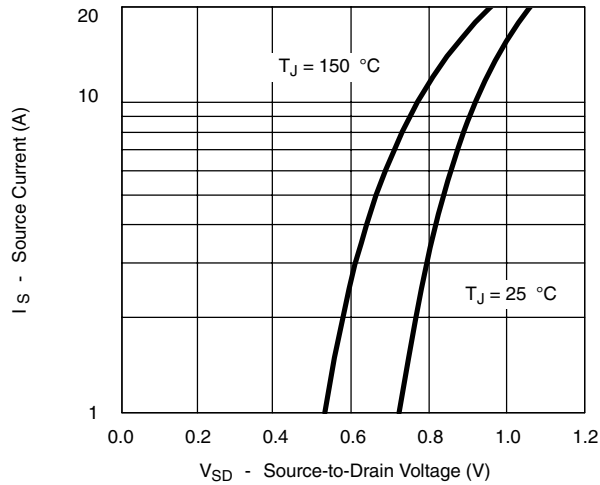
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power****Safe Operating Area, Junction-to-Ambient**

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

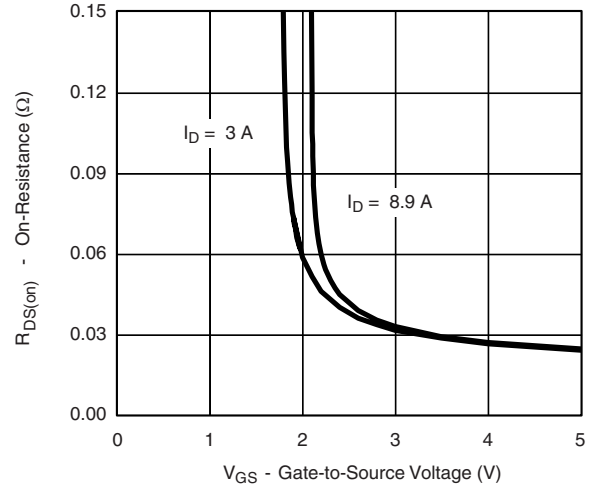


P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

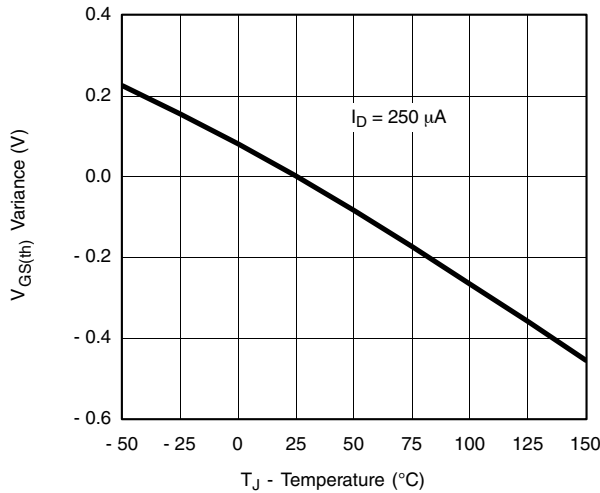
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



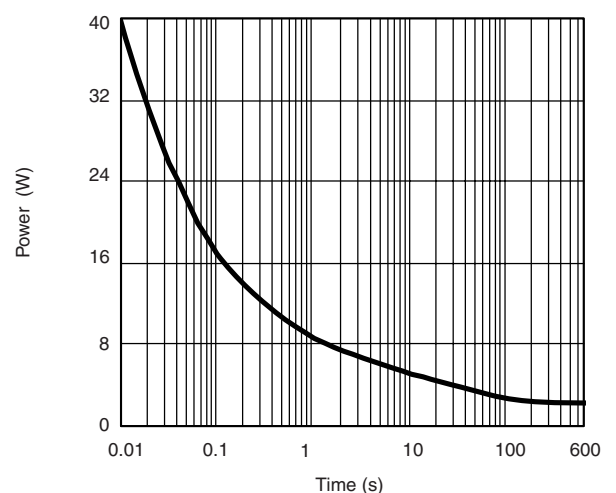
Source-Drain Diode Forward Voltage



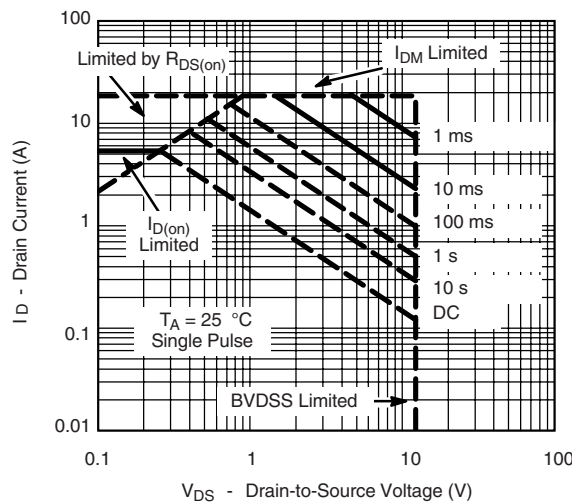
On-Resistance vs. Gate-to-Source Voltage



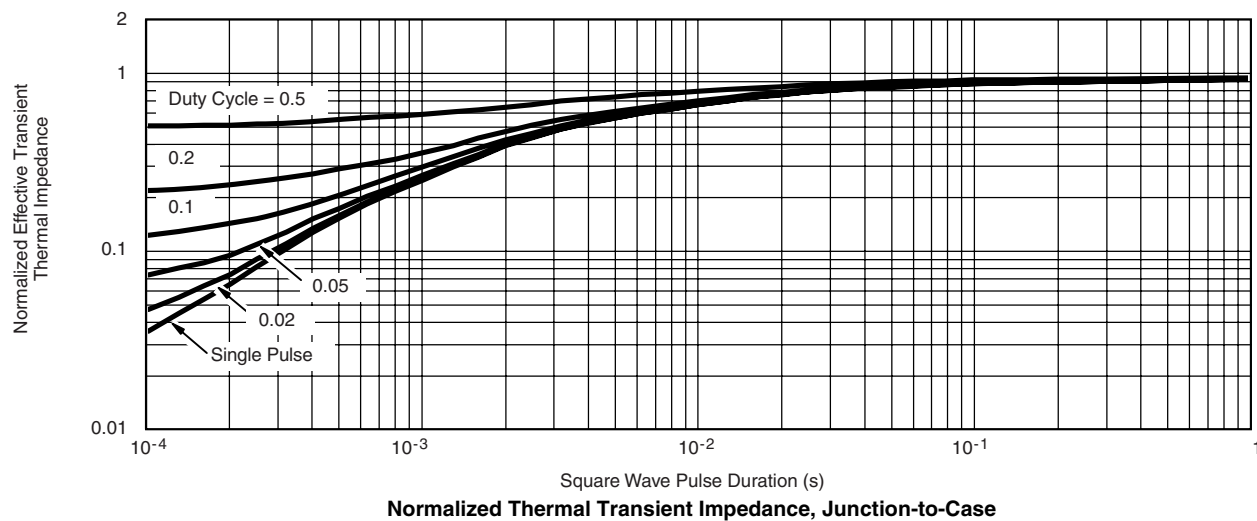
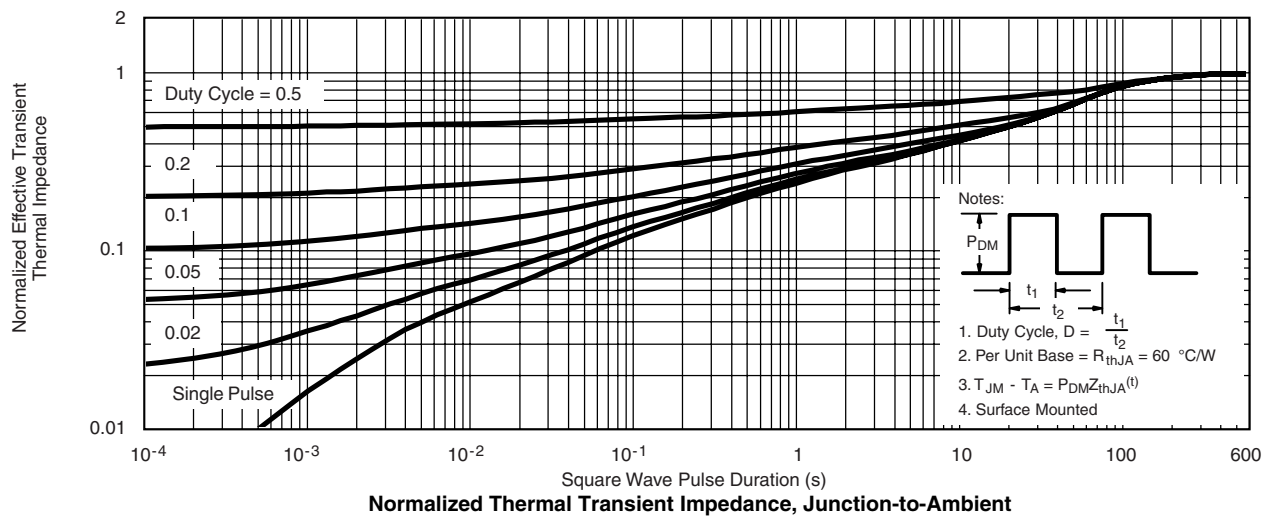
Threshold Voltage



Single Pulse Power

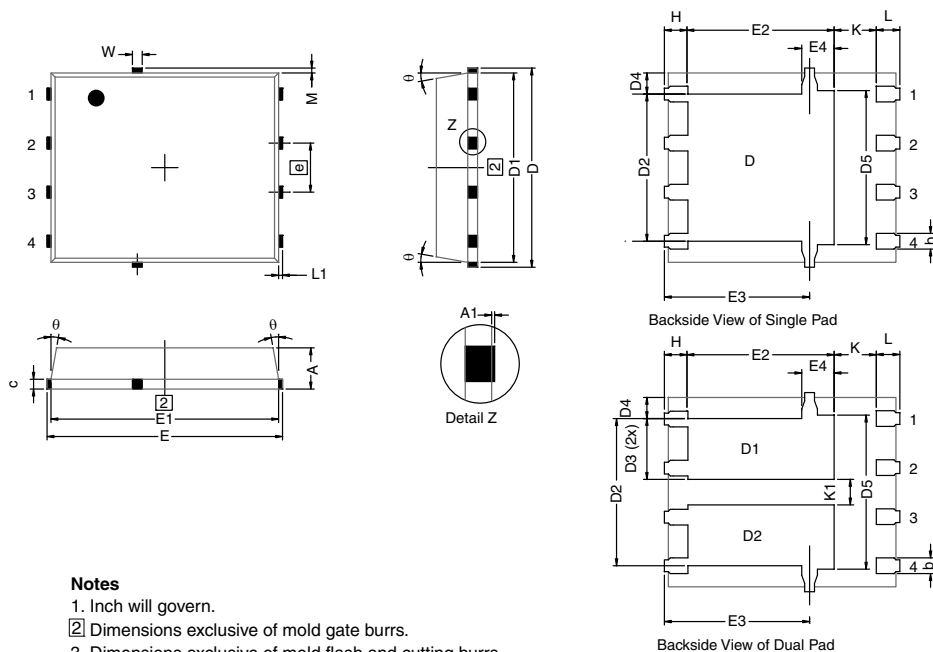


Safe Operating Area, Junction-to-Ambient

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

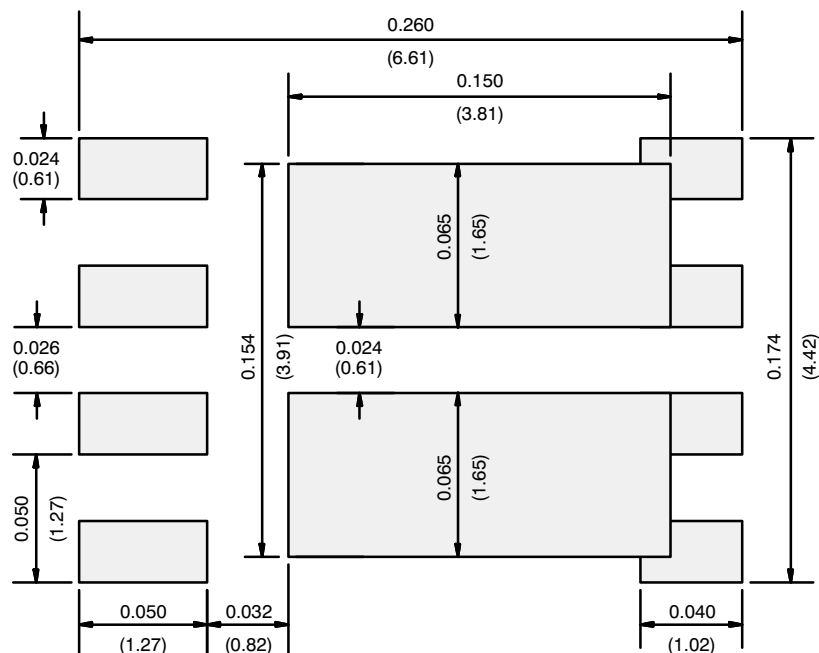
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PowerPAK® SO-8, (Single/Dual)



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.97	1.04	1.12	0.038	0.041	0.044
A1		-	0.05	0	-	0.002
b	0.33	0.41	0.51	0.013	0.016	0.020
c	0.23	0.28	0.33	0.009	0.011	0.013
D	5.05	5.15	5.26	0.199	0.203	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.56	3.76	3.91	0.140	0.148	0.154
D3	1.32	1.50	1.68	0.052	0.059	0.066
D4	0.57 typ.			0.0225 typ.		
D5	3.98 typ.			0.157 typ.		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	5.79	5.89	5.99	0.228	0.232	0.236
E2 (for AL product)	3.30	3.48	3.66	0.130	0.137	0.144
E2 (for other product)	3.48	3.66	3.84	0.137	0.144	0.151
E3	3.68	3.78	3.91	0.145	0.149	0.154
E4 (for AL product)	0.58 typ.			0.023 typ.		
E4 (for other product)	0.75 typ.			0.030 typ.		
e	1.27 BSC			0.050 BSC		
K (for AL product)	1.45 typ.			0.057 typ.		
K (for other product)	1.27 typ.			0.050 typ.		
K1	0.56	-	-	0.022	-	-
H	0.51	0.61	0.71	0.020	0.024	0.028
L	0.51	0.61	0.71	0.020	0.024	0.028
L1	0.06	0.13	0.20	0.002	0.005	0.008
θ	0°	-	12°	0°	-	12°
W	0.15	0.25	0.36	0.006	0.010	0.014
M	0.125 typ.			0.005 typ.		
ECN: C13-0702-Rev. K, 20-May-13						
DWG: 5881						

RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Dual



Recommended Minimum Pads
Dimensions in Inches/(mm)

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